

General Description:

The LWN2H550AT uses trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications. The package form is SOT23-6L, which accords with the ROHS standard and Halogen Free standard.

Features:

- Fast Switching
- Low Gate Charge and $R_{DS(ON)}$
- Low Reverse transfer capacitances

Applications:

- DC-DC converter
- Portable Equipment
- Power Management

100% DVDS Tested

100% Avalanche Tested



Package Marking and Ordering Information:

Marking	Part Number	Package	Packing	Qty.
N2H550A/D.C.	LWN2H550AT	SOT23-6L	Reel	3000 Pcs

Absolute Maximum Ratings:

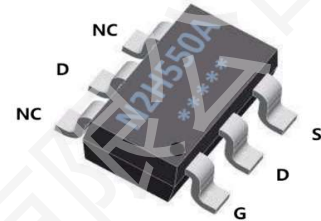
Symbol	Parameter		Value	Units
V_{DSS}	Drain-to-Source Voltage		200	V
I_D	Continuous Drain Current	$T_C=25^{\circ}\text{C}$	1.2	A
	Continuous Drain Current	$T_C=100^{\circ}\text{C}$	0.7	A
I_{DM}^{a1}	Pulsed Drain Current		4.8	A
E_{AS}^{a2}	Single pulse avalanche energy		1.0	mJ
V_{GS}	Gate-to-Source Voltage		± 20	V
P_D	Power Dissipation		1.6	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range		150, -55 to 150	$^{\circ}\text{C}$
T_L	Maximum Temperature for Soldering		260	$^{\circ}\text{C}$

Thermal Characteristics:

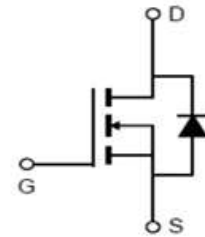
Symbol	Parameter	Value	Units
$R_{\theta JA}^{a3}$	Thermal Resistance, Junction-to-Ambient	78	$^{\circ}\text{C/W}$

V_{DSS}	200	V
I_D	1.2	A
P_D	1.6	W
$R_{DS(ON) \text{ TYPE}}$	450	$\text{m}\Omega$

Marking and Pin Assignment



Inner Equivalent Principium Chart



Electrical Characteristic ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified):

Static Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	200	--	--	V
I_{DSS}	Drain to Source Leakage Current	$V_{DS}=200V, V_{GS}=0V$	--	--	1.0	μA
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS}=+20V, V_{DS}=0V$	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS}=-20V, V_{DS}=0V$	--	--	-100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	2.0	3.0	V
$R_{DS(ON)}$	Drain-to-Source On-Resistance	$V_{GS}=10V, I_D=2.0A$	--	450	550	m Ω

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
C_{iss}	Input Capacitance	$V_{GS} = 0V$	--	461	--	pF
C_{oss}	Output Capacitance	$V_{DS} = 100V$	--	11.6	--	
C_{rss}	Reverse Transfer Capacitance	$f = 1.0MHz$	--	8.5	--	
R_G	Gate resistance	$V_{GS}=0V, V_{DS}=0V, f=1.0MHz$	--	1.4	--	Ω

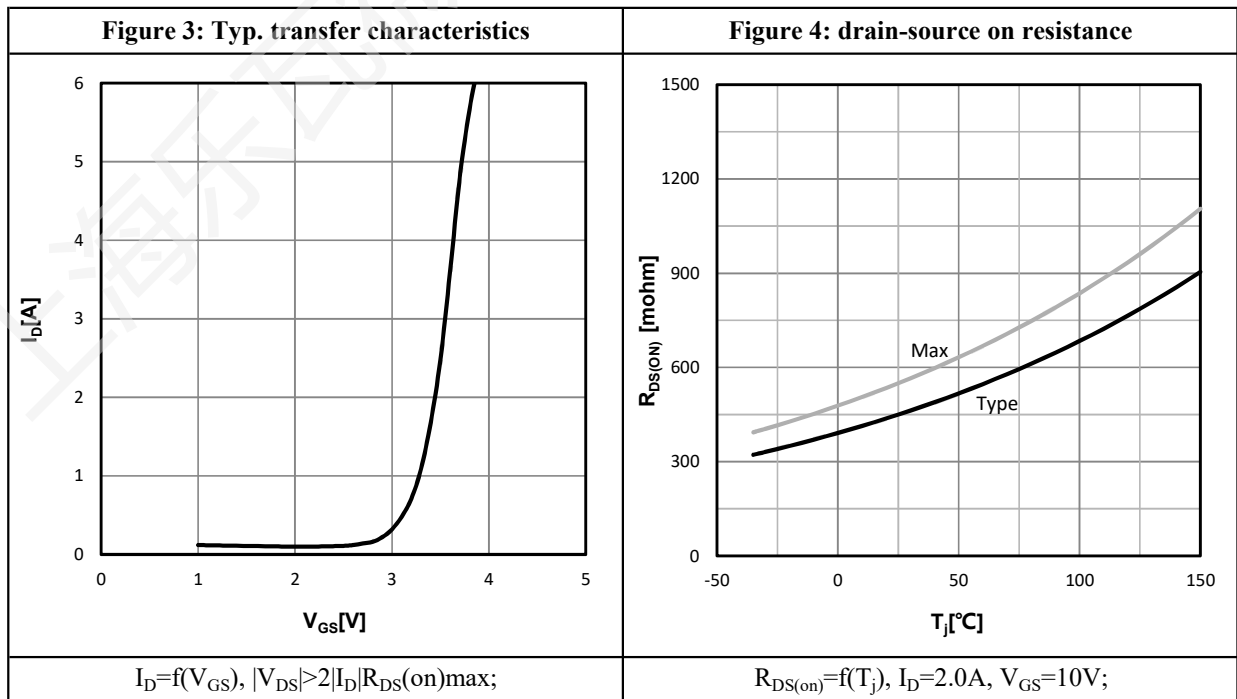
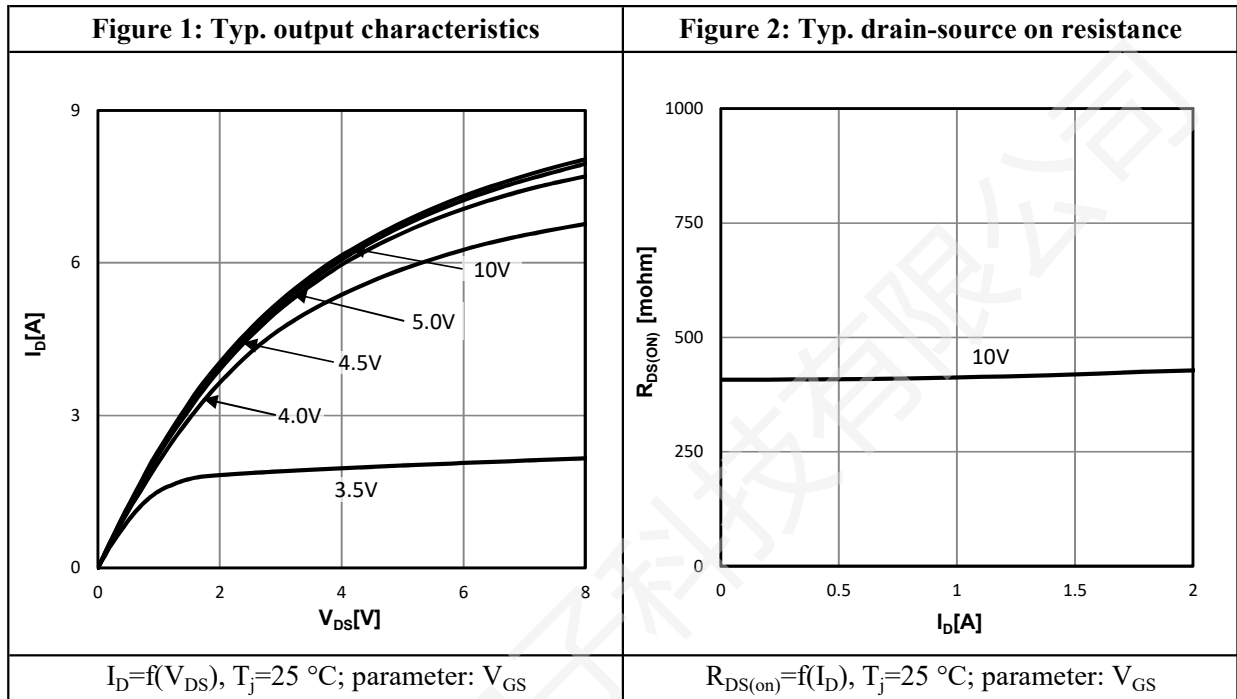
Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	$I_D=2.0A$	--	6.0	--	ns
t_r	Rise Time	$V_{DS}=100V$	--	7.0	--	
$t_{d(OFF)}$	Turn-Off Delay Time	$V_{GS}=10V$	--	17	--	
t_f	Fall Time	$R_G=4.0\Omega$	--	8.0	--	
Q_g	Total Gate Charge	$V_{GS}=10V$	--	12.5	--	nC
Q_{gs}	Gate Source Charge	$V_{DS}=100V$	--	1.8	--	
Q_{gd}	Gate Drain Charge	$I_D=2.0A$	--	2.9	--	

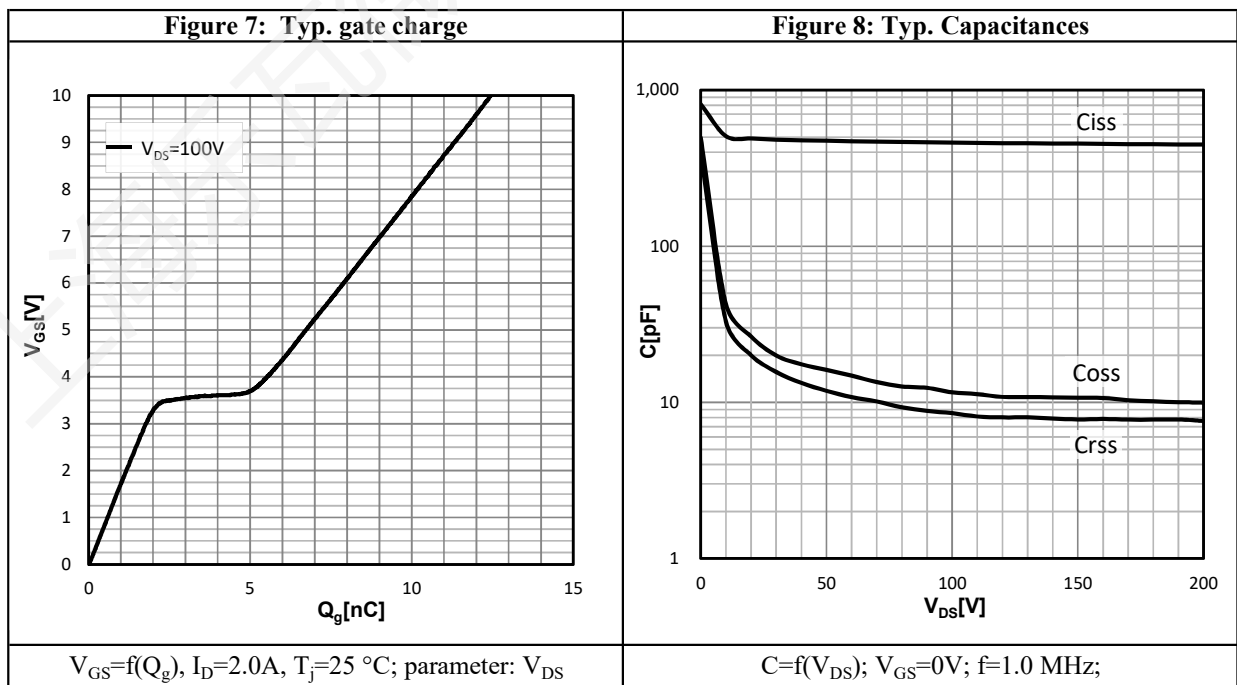
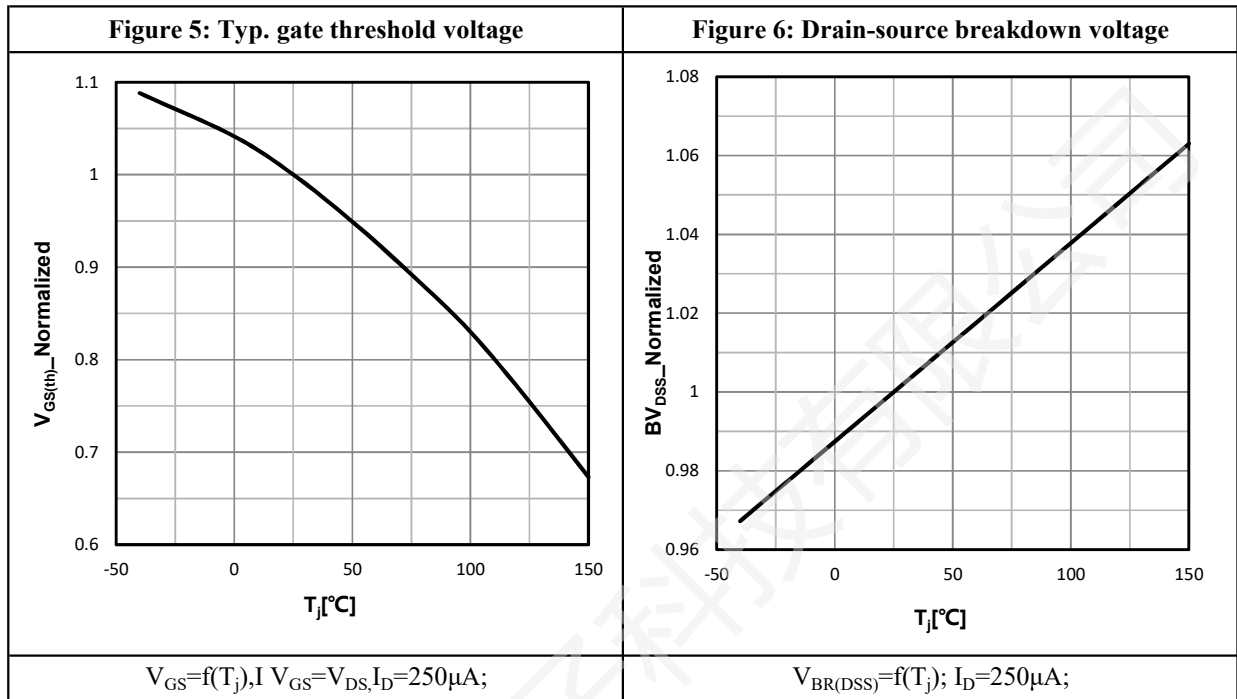
Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
I_S	Diode Forward Current	$T_C=25\text{ }^{\circ}\text{C}$	--	--	1.2	A
V_{SD}	Diode Forward Voltage	$I_S=2.0A, V_{GS}=0V$	--	--	1.2	V
t_{rr}	Reverse Recovery time	$I_S=2.0A, V_{DD}=100V$	--	75	--	ns
Q_{rr}	Reverse Recovery Charge	$dI/dt=100A/\mu s$	--	198	--	nC

a1: Repetitive rating; pulse width limited by maximum junction temperature

a2: $V_{DD}=100V, L=0.1mH, R_G=25\Omega$, Starting $T_j=25^{\circ}\text{C}$

a3: Surface Mounted on FR4 Board, $t \leq 10\text{sec}$

Characteristics Curve:




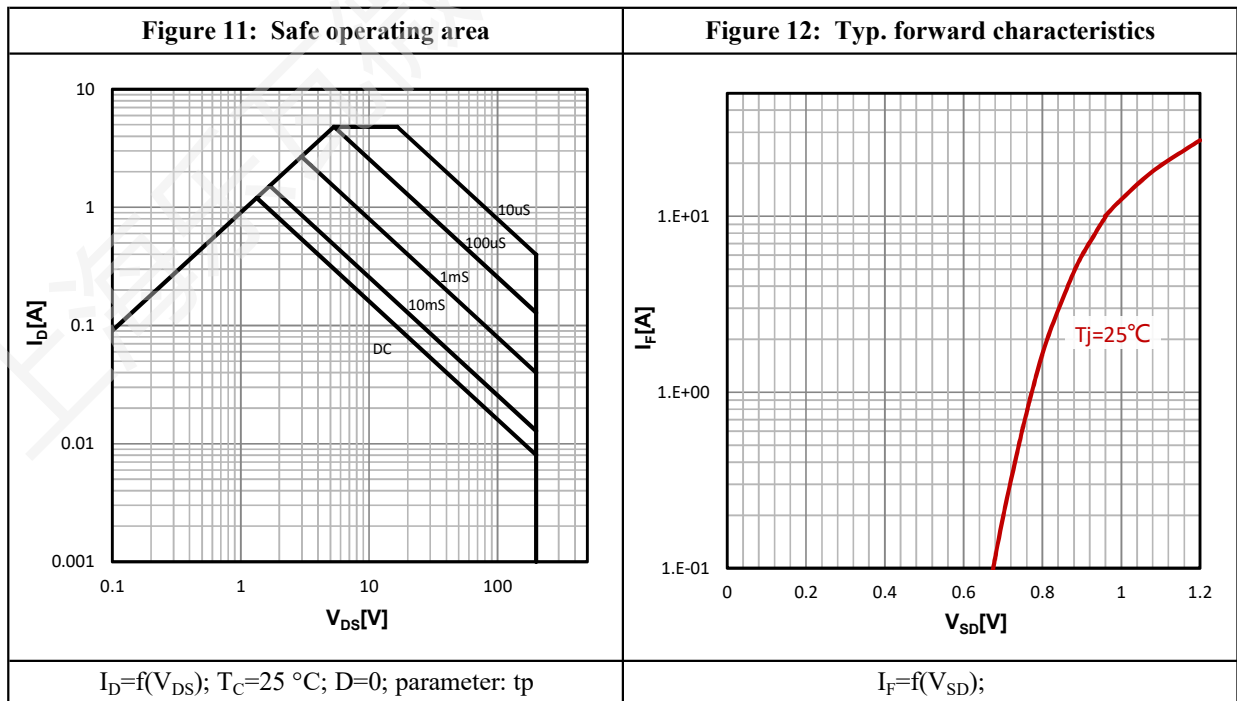
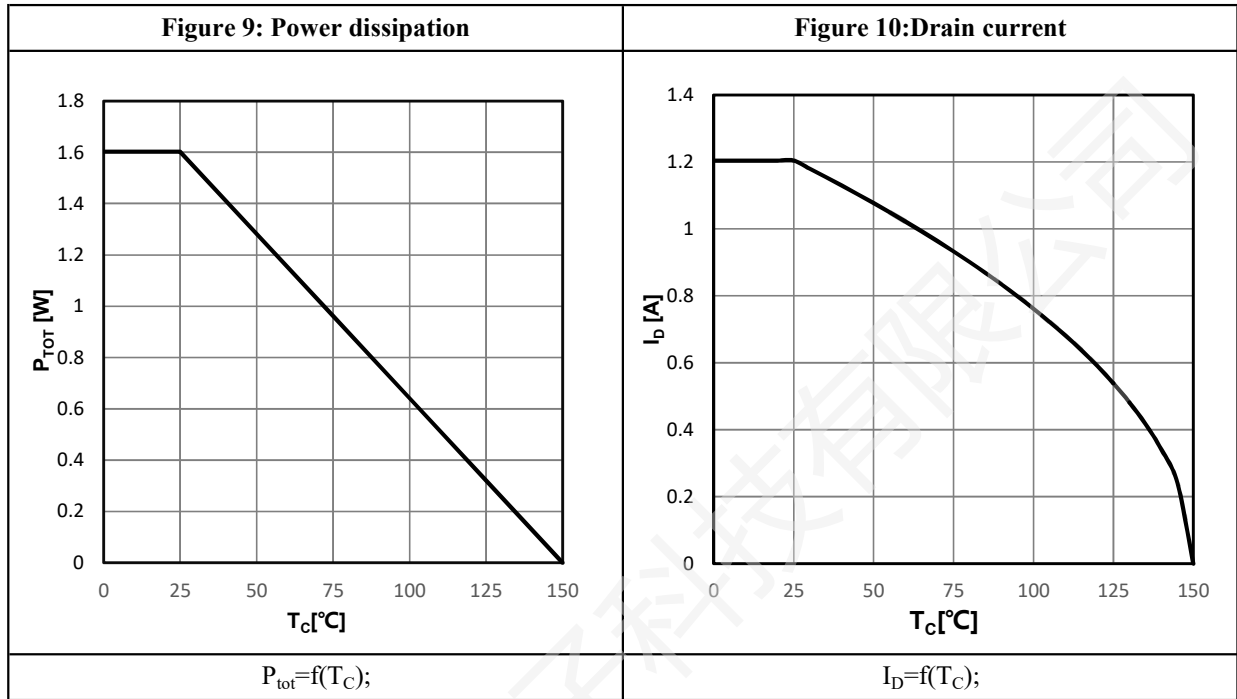
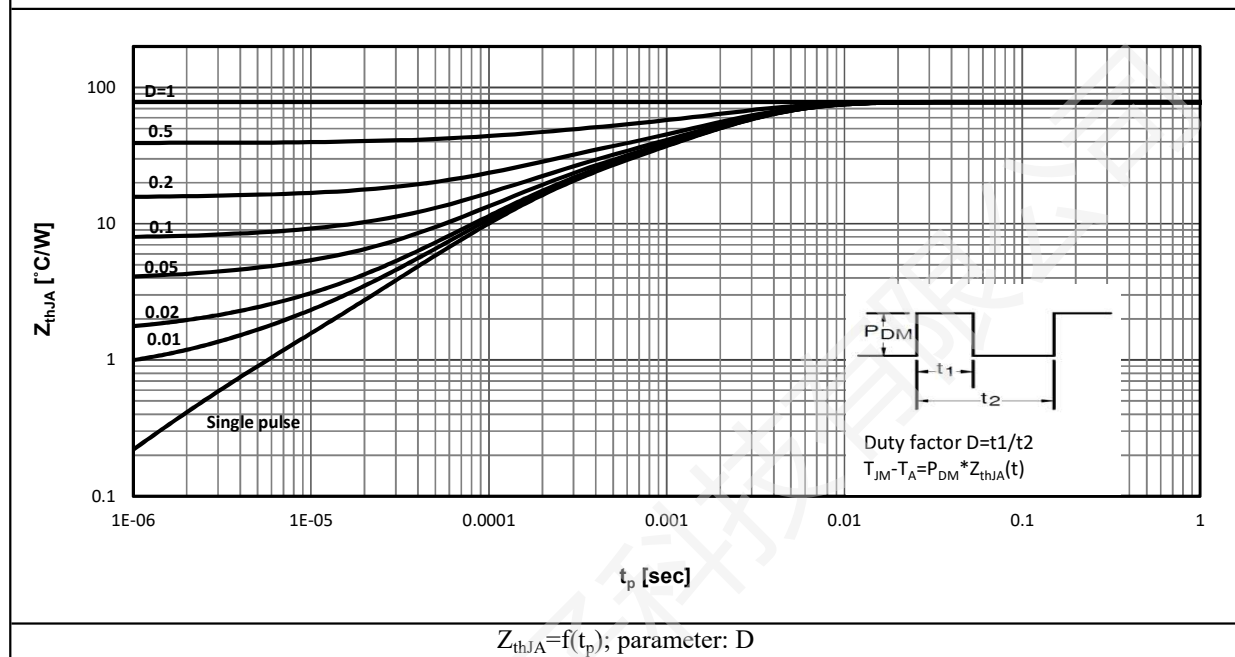
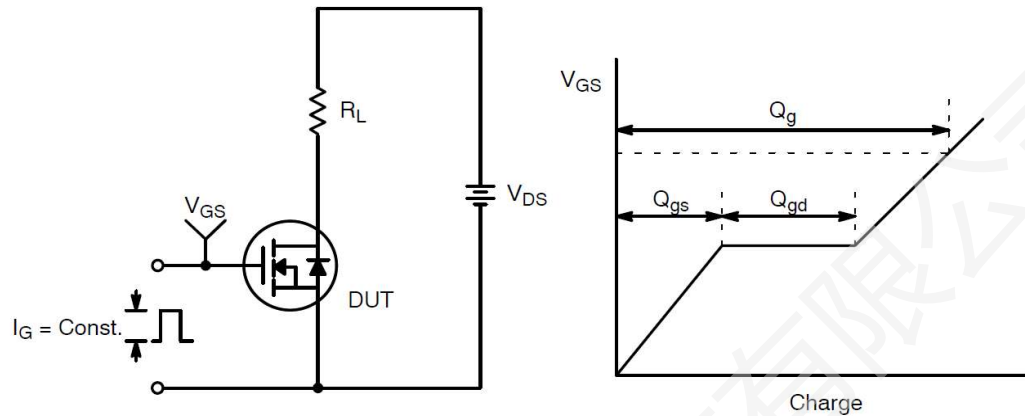
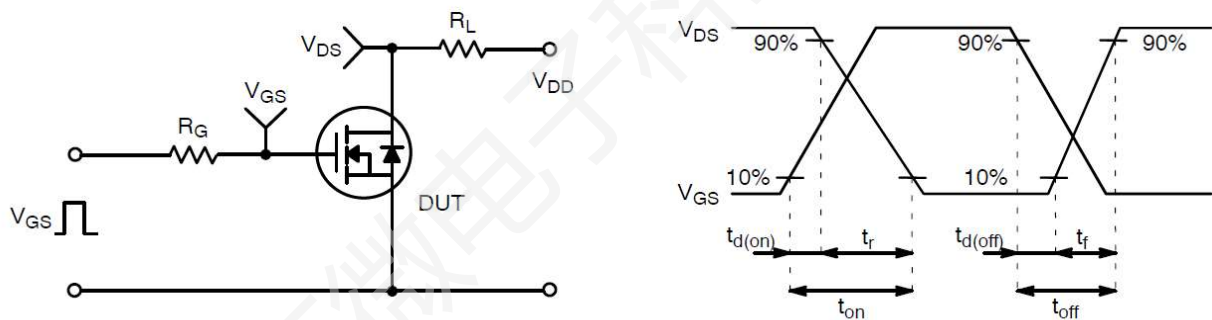
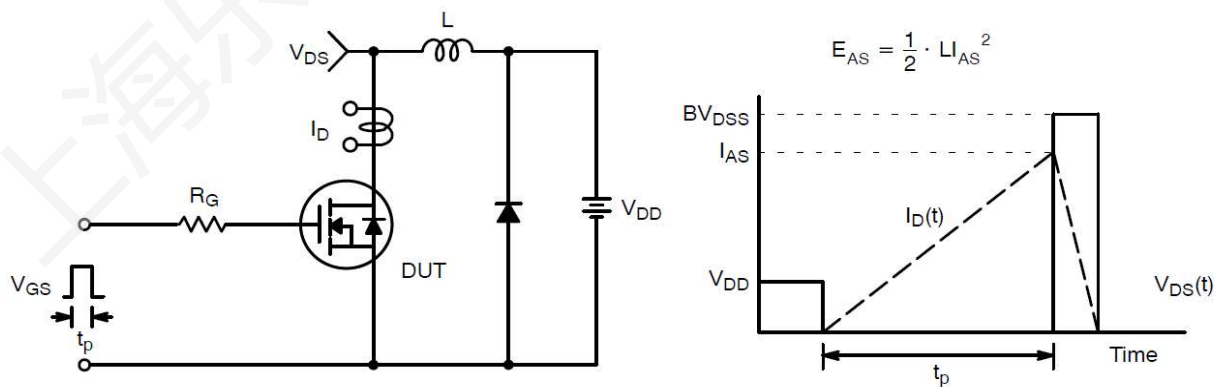
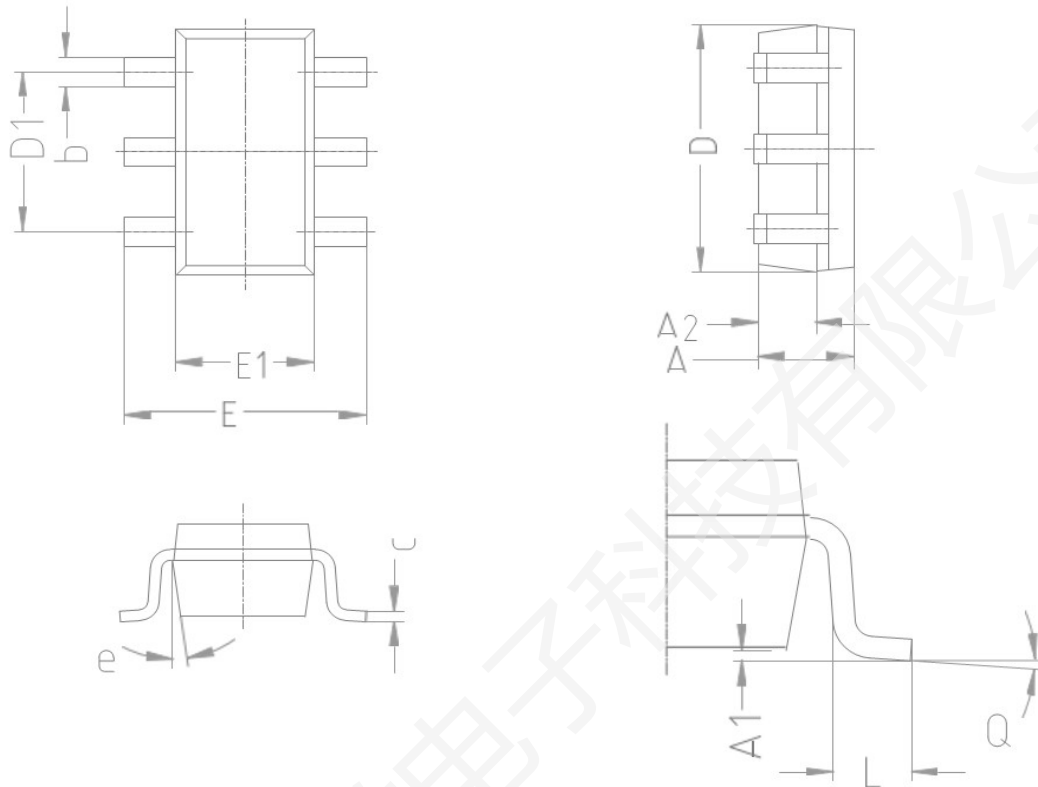


Figure 13: Max. Transient Thermal Impedance



Test Circuit & Waveform:

Figure 14: Gate Charge Test Circuit & Waveform

Figure 15: Resistive Switching Test Circuit & Waveforms

Figure 16: Unclamped Inductive Switching Test Circuit & Waveforms

Package Outline:


COMMON DIMENSION (MM)			
PKG	SOT23-6L		
Symbol	MIN	NOM	MAX
A	1.050	1.100	1.150
A1	0.010	0.060	0.150
A2	0.640	0.670	0.700
b	0.300	0.350	0.400
c	0.125	0.150	0.175
D	2.870	2.925	2.980
D1	1.800	1.900	2.000
E	2.650	2.800	2.950
E1	1.550	1.610	1.670
L	0.300	0.450	0.600
e	8°		
Q	0°	4°	8°

Revision History:

Revision	Date	Descriptions
Rev 1.1	July.2025	Initial Version

Disclaimer:

The information in this document is believed to be accurate and reliable. However, no responsibility is assumed by LW-Micro for its use. All operating parameters must be designed, validated and tested to ensure they meet the requirements of your application. LW-Micro reserves the right to make any specification and/or circuitry changes without prior notification. Before starting a brand-new project, please contact LW-Micro Sales to get the most recent relevant information.

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